

transistor and having a high concentration than said first impurity region; and

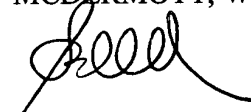
As amended
forming a storage node electrically connected to said second impurity region through said contact hole.--.

REMARKS

The above preliminary amendment is necessary to add new claims and to incorporate the data about parent applications and the amendments that were made in parent application Serial No. 09/119,053. Entry of the preliminary amendment is respectfully requested.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Stephen A. Becker
Registration No. 26,527

600 13th Street, N.W.
Washington, DC 20005-3096
(202) 756-8000 SAB:BD
Date: January 24, 2002
Facsimile: (202) 756-8087

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